



ACE4441B

P-Channel Enhancement Mode Field Effect Transistor

Description

The ACE4441B uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge. This device is suitable for use as a load switch or in PWM applications.

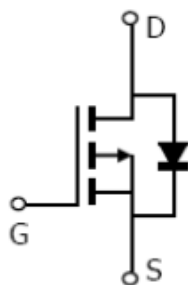
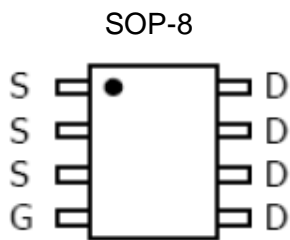
Features

- $V_{DS}(V)=-60V$
- $I_D=-4A$ ($V_{GS}=-10V$)
- $R_{DS(ON)} < 75m\Omega$ ($V_{GS}=-10V$)
- $R_{DS(ON)} < 90m\Omega$ ($V_{GS}=-4.5V$)

Absolute Maximum Ratings

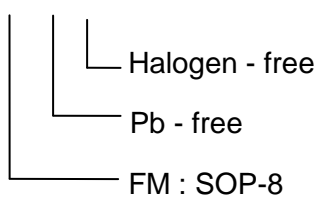
| Parameter | Symbol | Max | Unit |
|---|----------------|------------------|------------|
| Drain-Source Voltage | V_{DS} | -60 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current (Continuous) * AC | I_D | $T_A=25^\circ C$ | -4 |
| | | $T_A=70^\circ C$ | -3.2 |
| Drain Current (Pulse) * B | I_{DM} | -20 | A |
| Power Dissipation | P_D | $T_A=25^\circ C$ | 3 |
| | | $T_A=70^\circ C$ | 2.1 |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | $^\circ C$ |

Packaging Type



Ordering information

ACE4441B XX + H





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Electrical Characteristics

$T_A=25\text{ }^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|---------------------------------------|---------------|--|------|-------|------|------------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}=0V, I_D=-250\mu A$ | -60 | | | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=-48V, V_{GS}=0V$ | | | -1 | μA |
| Gate Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | | | 100 | nA |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | $V_{GS}=-10V, I_D=-4.5A$ | | 64 | 75 | m Ω |
| | | $V_{GS}=-4.5V, I_D=-3.5A$ | | 79 | 90 | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_{DS}=-250\mu A$ | -1.0 | -1.7 | -2.5 | V |
| Forward Transconductance | g_{FS} | $V_{GS}=-10V, I_D=-7A$ | | 9 | | S |
| Diode Forward Voltage | V_{SD} | $I_{SD}=-1A, V_{GS}=0V$ | | -0.76 | -1 | V |
| Maximum Body-Diode Continuous Current | I_S | | | | -3 | A |
| Switching | | | | | | |
| Total Gate Charge | Q_g | $V_{DS}=-30V, I_D=-7A$ $V_{GS}=-10V$ | | 15 | 19 | nC |
| Gate-Source Charge | Q_{gs} | | | 2.5 | | |
| Gate-Drain Charge | Q_{gd} | | | 3 | | |
| Turn-On Delay Time | $T_{d(on)}$ | $V_{DS}=-30V, R_L=10\Omega,$ $V_{GS}=-10V, R_{GEN}=3\Omega$ | | 8 | 16 | ns |
| Turn-On Rise Time | t_f | | | 3.8 | 7.6 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 31.5 | 63 | |
| Turn-Off Fall Time | t_f | | | 7.5 | 15 | |
| Dynamic | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=-30V, V_{GS}=0V$ $f=1MHz$ | | 760 | | pF |
| Output Capacitance | C_{oss} | | | 90 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 40 | | |

Note: 1. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25\text{ }^\circ\text{C}$. The value in any given application depends on the user's specific board design.

2. Repetitive rating, pulse width limited by junction temperature.

3. The current rating is based on the $t \leq 10s$ junction to ambient thermal resistance rating.



Typical Performance Characteristics

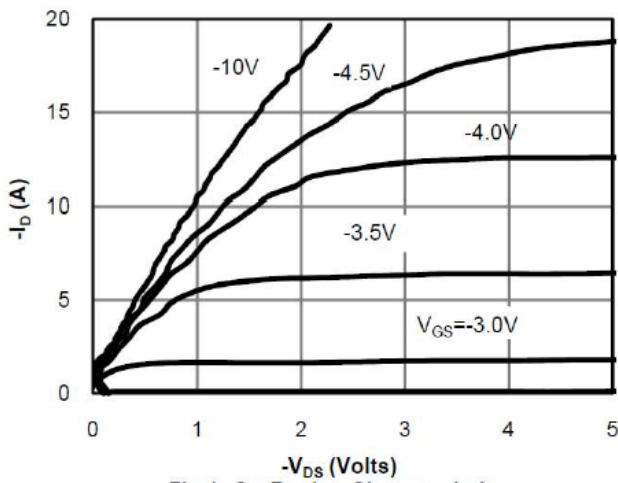


Fig 1: On-Region Characteristics

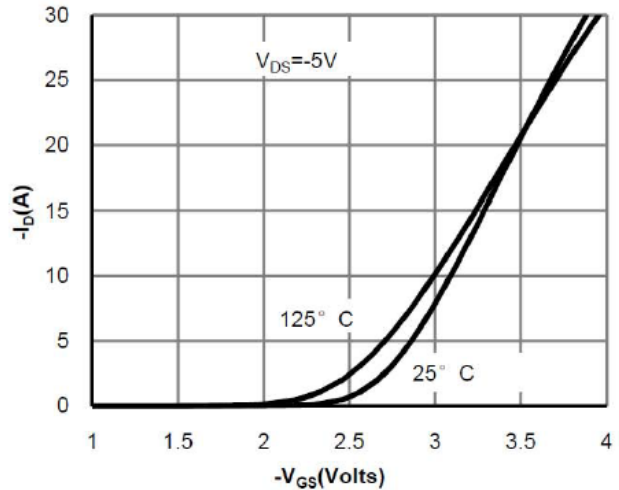


Figure 2: Transfer Characteristics

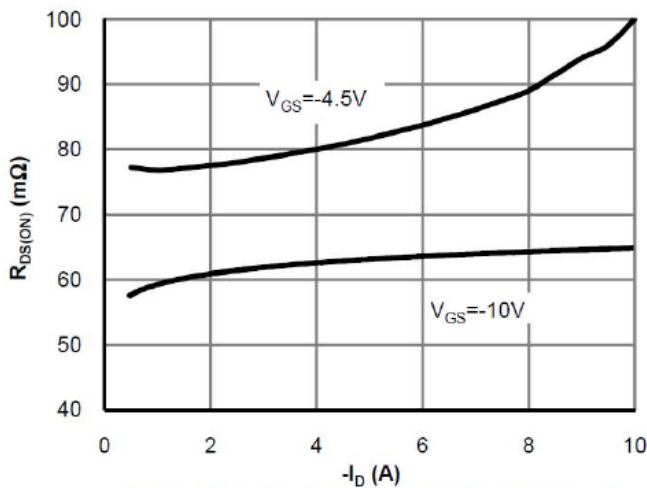


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

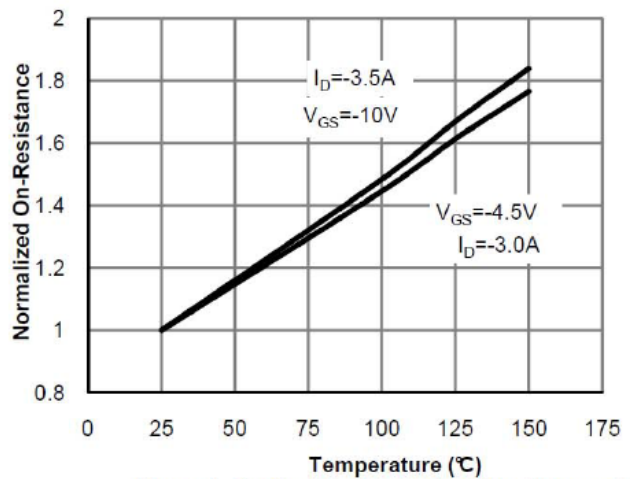


Figure 4: On-Resistance vs. Junction Temperature

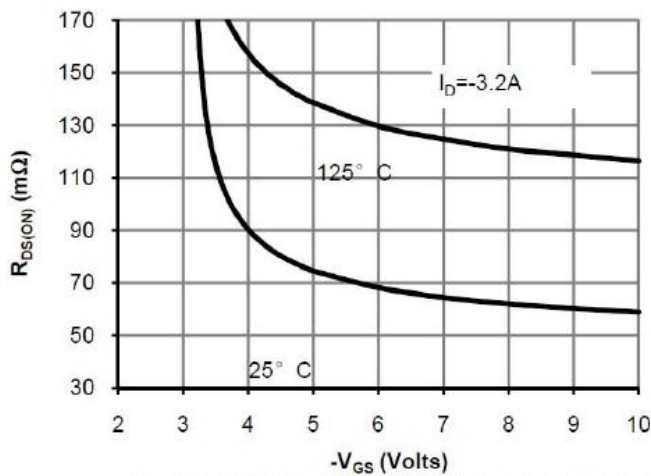


Figure 5: On-Resistance vs. Gate-Source Voltage

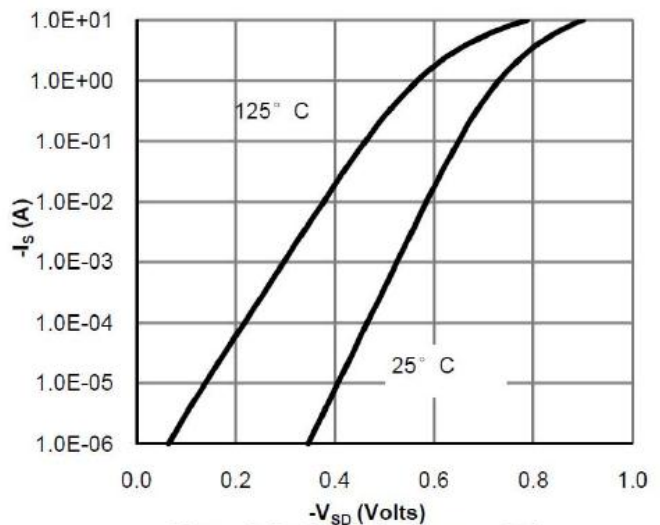


Figure 6: Body-Diode Characteristics



Typical Performance Characteristics

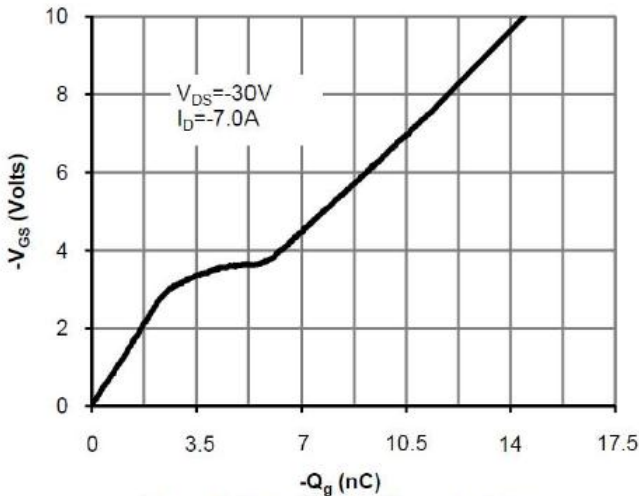


Figure 7: Gate-Charge Characteristics

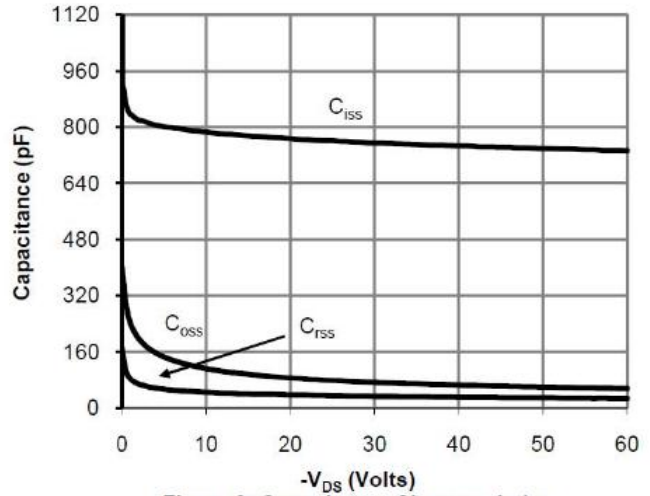


Figure 8: Capacitance Characteristics

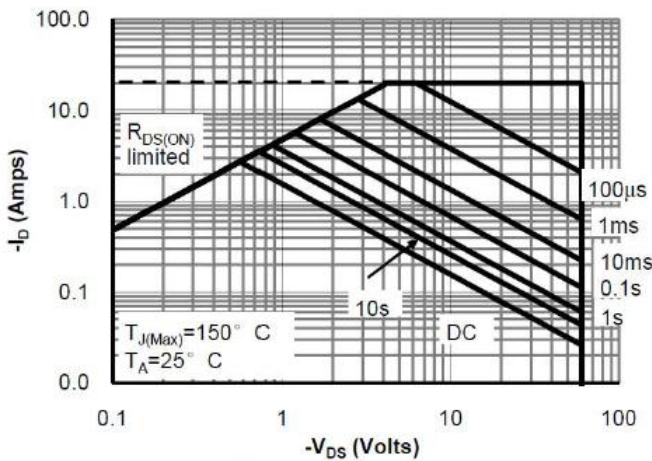


Figure 9: Maximum Forward Biased Safe Operating Area

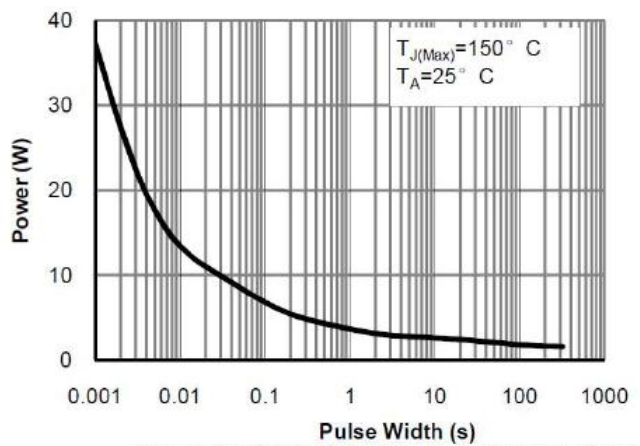


Figure 10: Single Pulse Power Rating Junction-to-Ambient

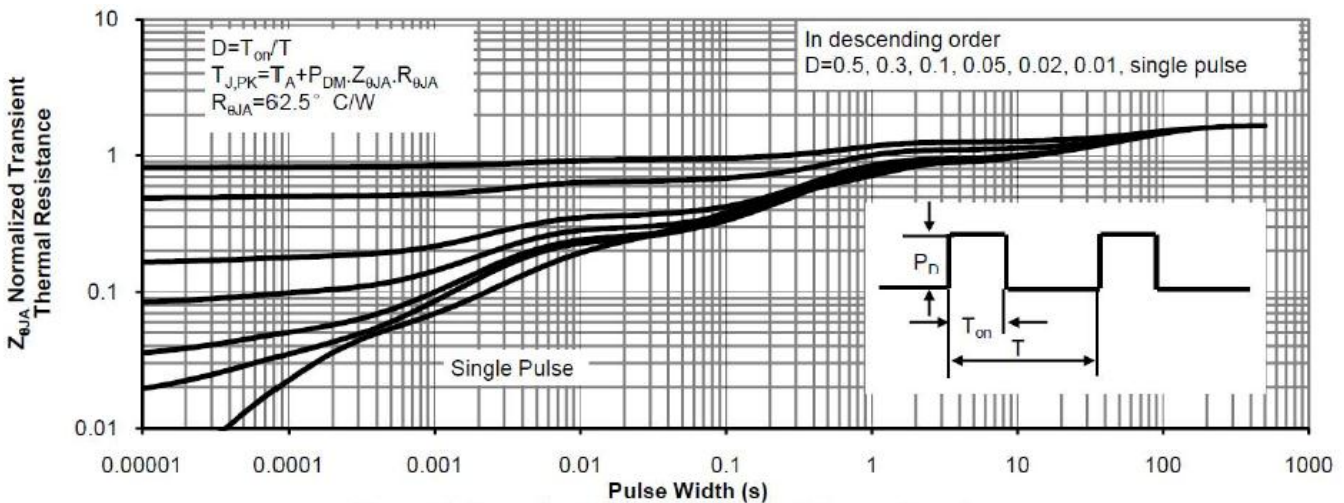


Figure 11: Normalized Maximum Transient Thermal Impedance

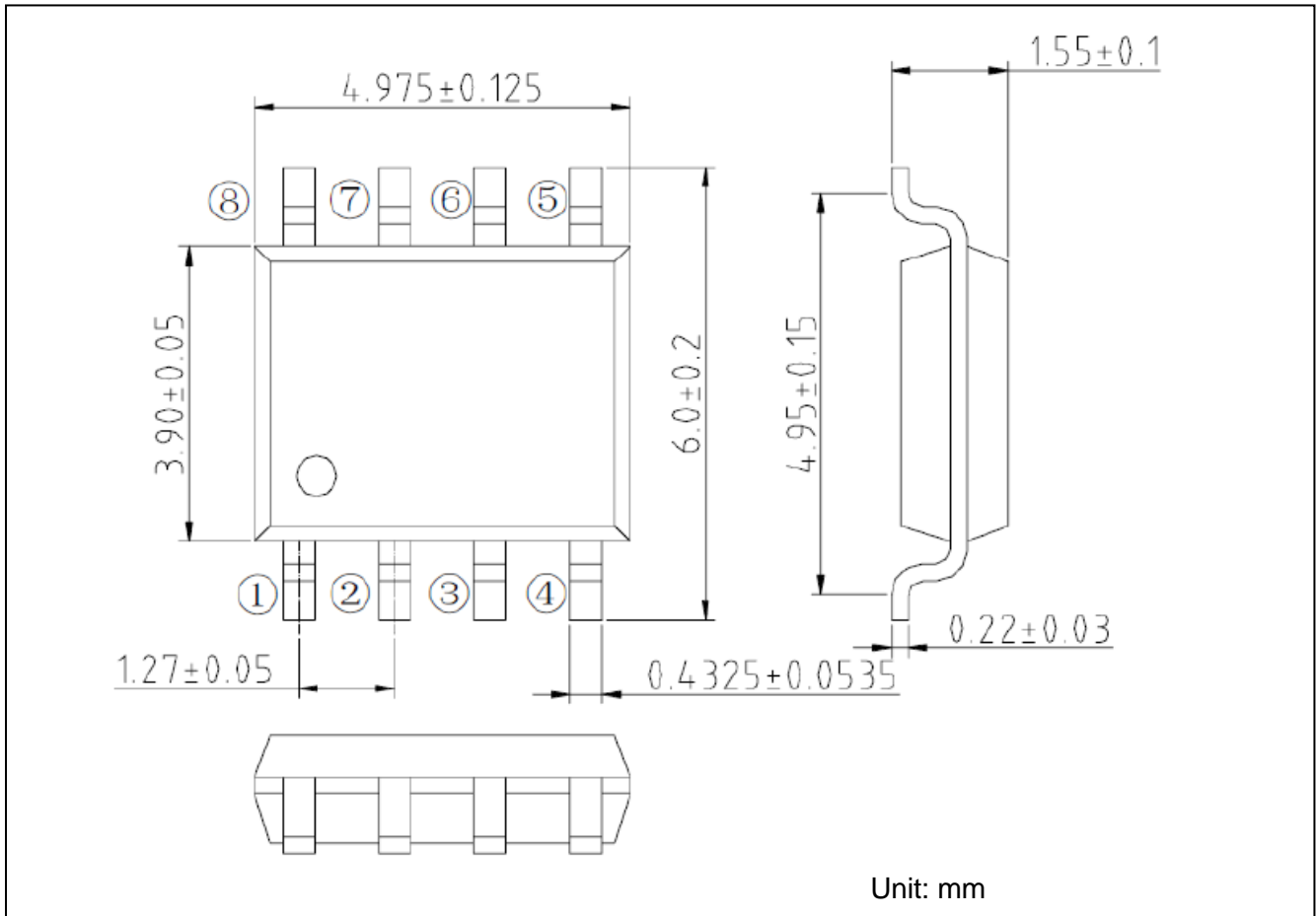


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Packing Information

SOP-8





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Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD.

As sued herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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